

Dual General Purpose Transistors

PNP Duals

BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G, SBC857BDW1T1G Series, BC858CDW1T1G Series

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-----------|-------------------|------|
| Collector - Emitter Voltage BC856, SBC856 BC857, SBC857 BC858 | V_{CEO} | -65 -45 -30 | V |
| Collector - Base Voltage BC856, SBC856 BC857, SBC857 BC858 | V_{CBO} | -80 -50 -30 | V |
| Emitter - Base Voltage | V_{EBO} | -5.0 | V |
| Collector Current - Continuous | I_C | -100 | mAdc |
| Collector Current - Peak | I_C | -200 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------------|----------------------------------|
| Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25\text{ }^\circ\text{C}$ Derate Above $25\text{ }^\circ\text{C}$ | P_D | 380 250 3.0 | mW mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 328 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

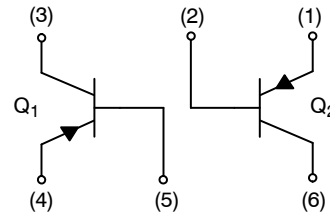
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in

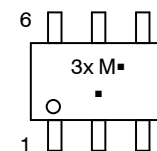
*For additional information on our Pb-Free strategy and soldering details, please download the [onsemi Soldering and Mounting Techniques Reference Manual, SOLDEPRM/D](#).



SOT-363/SC-88
CASE 419B
STYLE 1



MARKING DIAGRAM



- 3x = Specific Device Code
x = B, F, G, or L
(See Ordering Information)
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 6.

BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G, SBC857BDW1T1G Series, BC858CDW1T1G Series

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|---------------|----------------------|-------------|-------------|---------------------|
| OFF CHARACTERISTICS | | | | | |
| Collector - Emitter Breakdown Voltage ($I_C = -10\text{ mA}$) BC856, SBC856 Series BC857, SBC857 Series BC858 Series | $V_{(BR)CEO}$ | -65 -45 -30 | - - - | - - - | V |
| Collector - Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$) BC856, SBC856 Series BC857B, SBC857B Only BC858 Series | $V_{(BR)CES}$ | -80 -50 -30 | - - - | - - - | V |
| Collector - Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$) BC856, SBC856 Series BC857, SBC857 Series BC858 Series | $V_{(BR)CBO}$ | -80 -50 -30 | - - - | - - - | V |
| Emitter - Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$) BC856, SBC856 Series BC857, SBC857 Series BC858 Series | $V_{(BR)EBO}$ | -5.0 -5.0 -5.0 | - - - | - - - | V |
| Collector Cutoff Current ($V_{CB} = -30\text{ V}$) ($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$) | I_{CBO} | - - | - - | -15 -4.0 | nA μA |

ON CHARACTERISTICS

| | | | | | |
|---|---------------|----------------------|--------------------------|----------------------|---|
| DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$) BC856B, SBC856B, BC857B, SBC857B BC857C, SBC857C, BC858C ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) BC856B, SBC856B, BC857B, SBC857B BC857C, SBC857C, BC858C | h_{FE} | - - 220 420 | 150 270 290 520 | - - 475 800 | - |
| Collector - Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$) | $V_{CE(sat)}$ | - - | - - | -0.3 -0.65 | V |
| Base - Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$) | $V_{BE(sat)}$ | - - | -0.7 -0.9 | - - | V |
| Base - Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$) | $V_{BE(on)}$ | -0.6 - | - - | -0.75 -0.82 | V |

SMALL-SIGNAL CHARACTERISTICS

| | | | | | |
|--|----------|-----|---|-----|-----|
| Current - Gain - Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $f = 100\text{ MHz}$) | f_T | 100 | - | - | MHz |
| Output Capacitance ($V_{CB} = -10\text{ V}$, $f = 1.0\text{ MHz}$) | C_{ob} | - | - | 4.5 | pF |
| Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$) | NF | - | - | 10 | dB |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G, SBC857BDW1T1G Series, BC858CDW1T1G Series

TYPICAL CHARACTERISTICS – BC856/SBC856

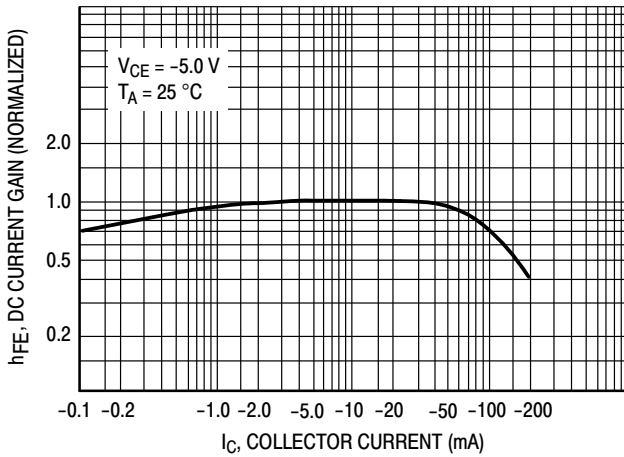


Figure 1. DC Current Gain

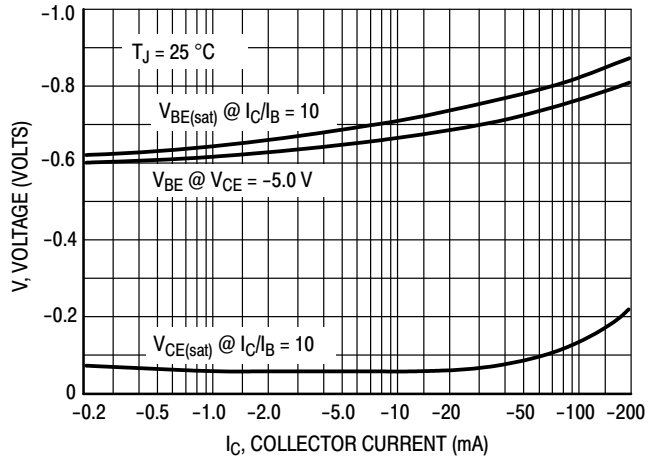


Figure 2. "On" Voltage

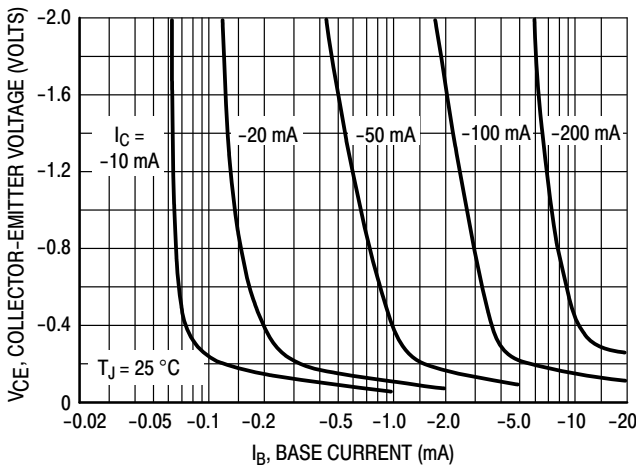


Figure 3. Collector Saturation Region

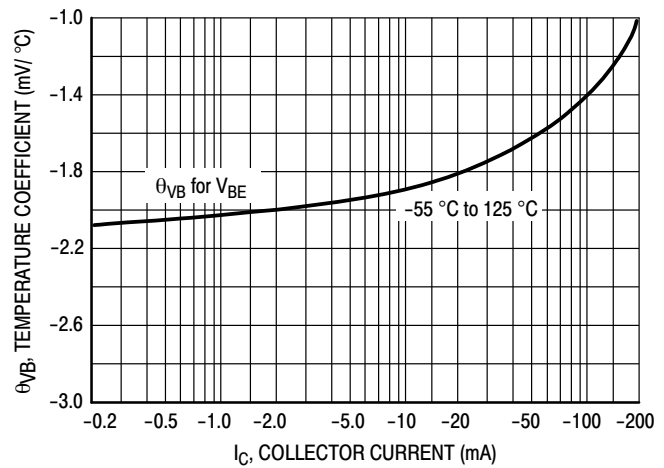


Figure 4. Base-Emitter Temperature Coefficient

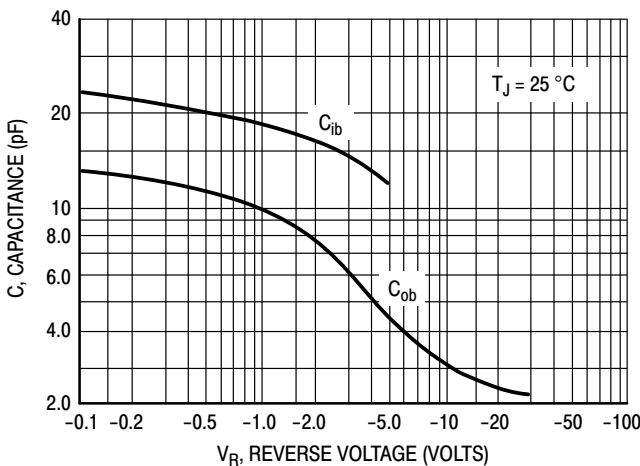


Figure 5. Capacitance

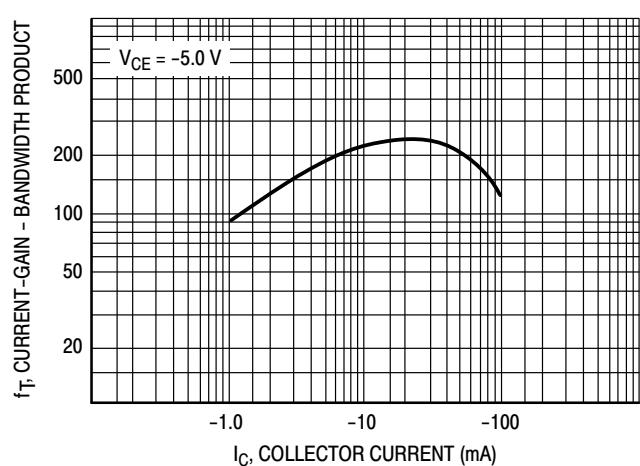


Figure 6. Current-Gain - Bandwidth Product

BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G, SBC857BDW1T1G Series, BC858CDW1T1G Series

TYPICAL CHARACTERISTICS – BC857/SBC857/BC858

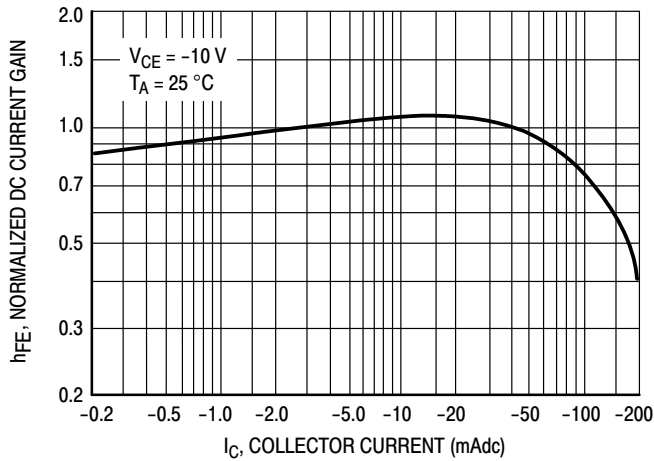


Figure 7. Normalized DC Current Gain

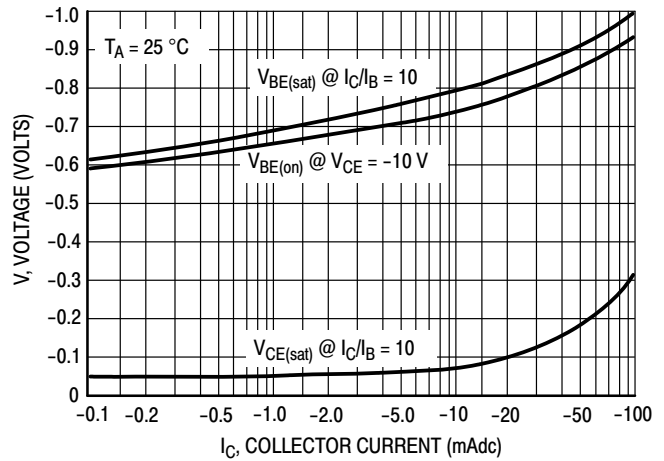


Figure 8. "Saturation" and "On" Voltages

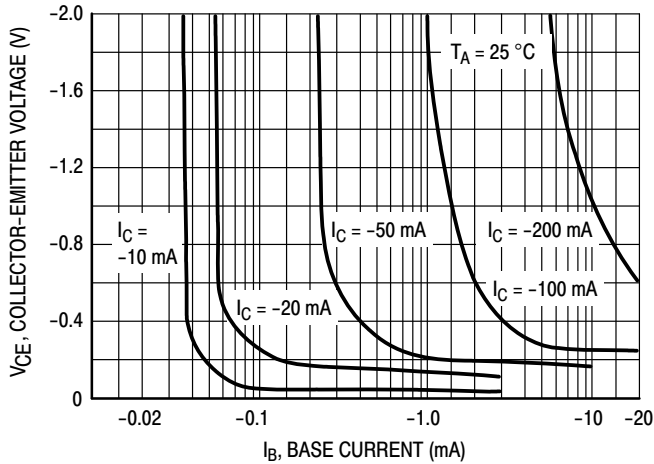


Figure 9. Collector Saturation Region

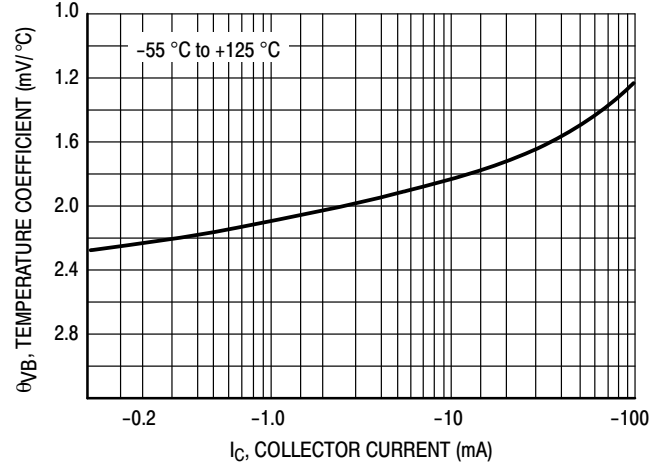


Figure 10. Base-Emitter Temperature Coefficient

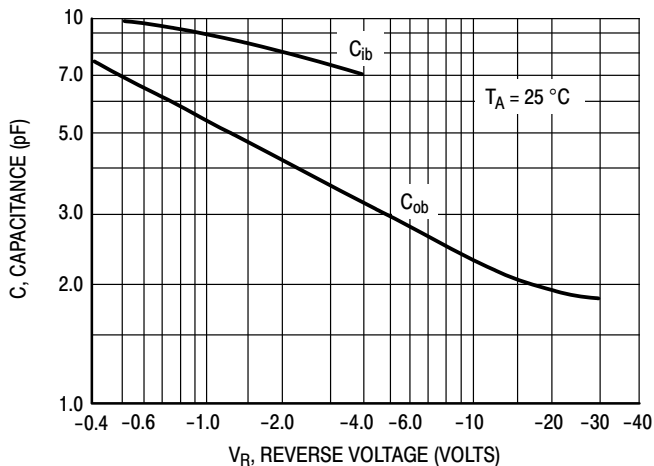


Figure 11. Capacitances

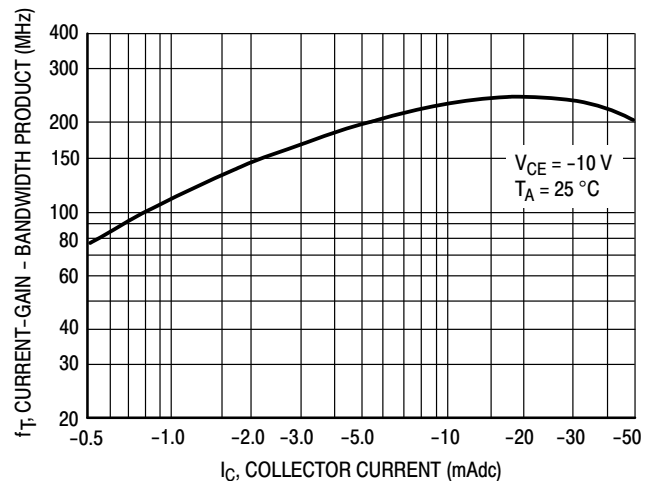


Figure 12. Current-Gain - Bandwidth Product

BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G, SBC857BDW1T1G Series, BC858CDW1T1G Series

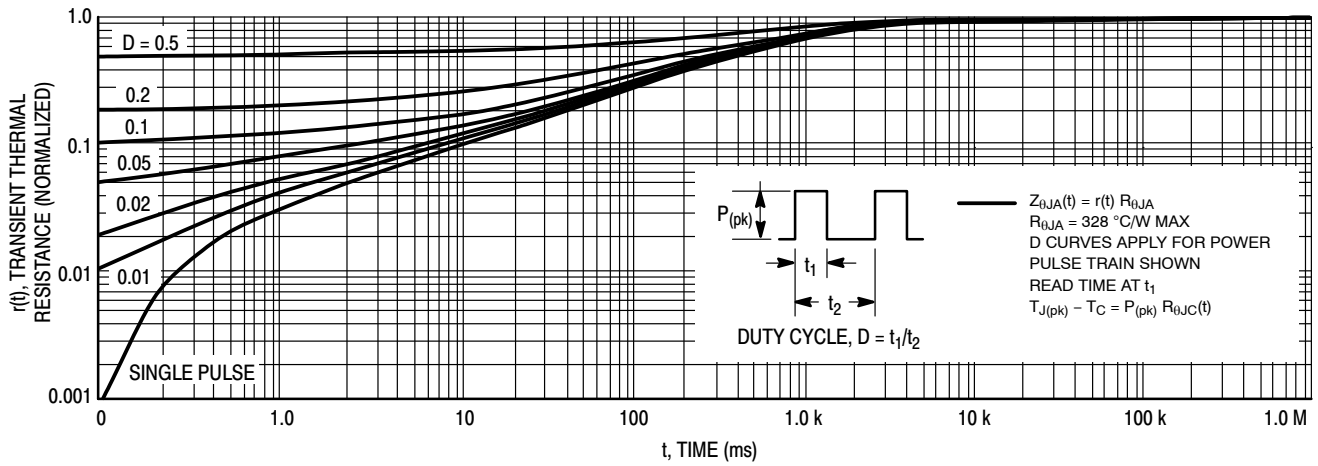


Figure 13. Thermal Response

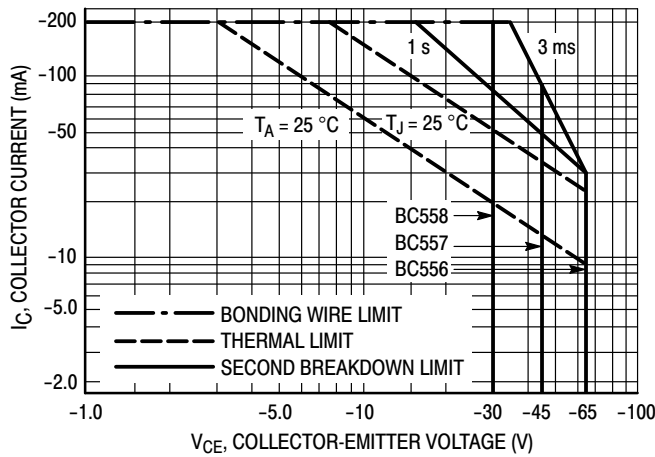


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150\text{ °C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150\text{ °C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G, SBC857BDW1T1G Series, BC858CDW1T1G Series

ORDERING INFORMATION

| Device | Device Marking | Package | Shipping [†] |
|---------------|----------------|----------------------|-----------------------|
| BC856BDW1T1G | 3B | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC856BDW1T1G | 3B | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| BC856BDW1T3G | 3B | SOT-363 (Pb-Free) | 10,000 / Tape & Reel |
| SBC856BDW1T3G | 3B | SOT-363 (Pb-Free) | 10,000 / Tape & Reel |
| BC857BDW1T1G | 3F | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC857BDW1T1G | 3F | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| BC857CDW1T1G | 3G | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC857CDW1T1G | 3G | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |

DISCONTINUED (Note 2)

| | | | |
|--------------|----|----------------------|---------------------|
| BC858CDW1T1G | 3L | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
|--------------|----|----------------------|---------------------|

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

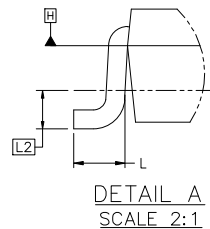
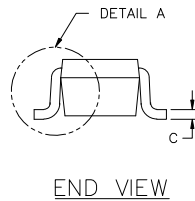
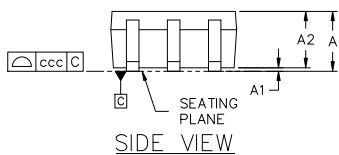
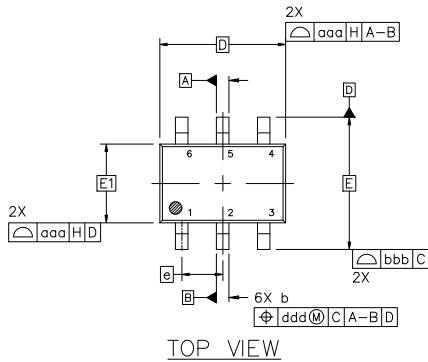


SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

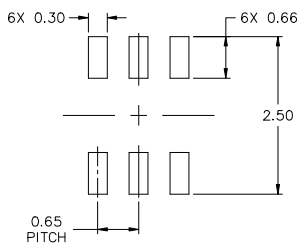
DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

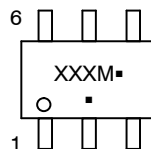


| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | --- | --- | 1.10 |
| A1 | 0.00 | --- | 0.10 |
| A2 | 0.70 | 0.90 | 1.00 |
| b | 0.15 | 0.20 | 0.25 |
| c | 0.08 | 0.15 | 0.22 |
| D | 2.00 BSC | | |
| E | 2.10 BSC | | |
| E1 | 1.25 BSC | | |
| e | 0.65 BSC | | |
| L | 0.26 | 0.36 | 0.46 |
| L2 | 0.15 BSC | | |
| aaa | 0.15 | | |
| bbb | 0.30 | | |
| ccc | 0.10 | | |
| ddd | 0.10 | | |



* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

| | | |
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SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

DATE 18 APR 2024

| | | | | | |
|---|---|--|--|--|--|
| STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2 | STYLE 2: CANCELLED | STYLE 3: CANCELLED | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2 |
| STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2 | STYLE 8: CANCELLED | STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2 | STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2 | STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2 | STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2 |
| STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC | STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1 | STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1 | STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1 | STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1 |
| STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF | STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR | STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1 | STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c) | STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C | STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE |
| STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1 | STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1 | STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2 | STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN | STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE | STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

| | | |
|-------------------------|------------------------------------|---|
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